

General Description

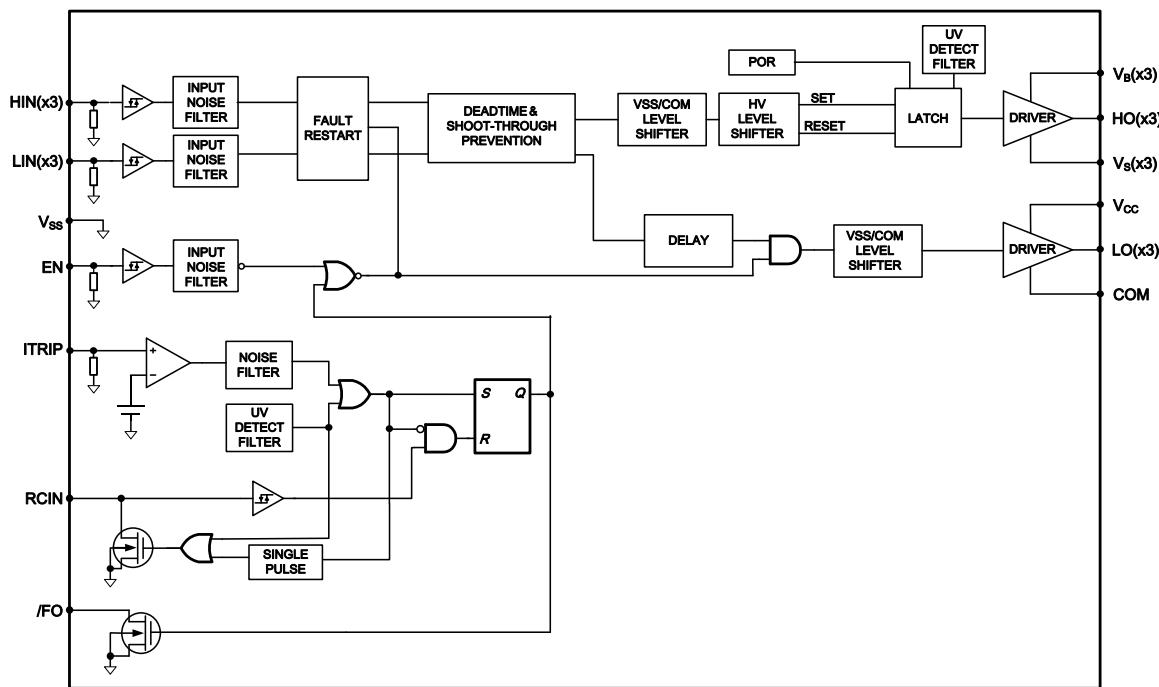
The AGD8156A / AGD8256A are 600V 6-channel gate drivers ICs to control IGBTs and power MOS-transistors in 3-phase inverter systems. Due to specially designed common mode filter, it has an excellent ruggedness on transient voltage variation.



SOP-28L
(Body: 18 x 7.5 x 2.5 mm)



Internal Block Diagram



Features

- Maximum blocking voltage +600V
- Output current: +200mA / -350mA (Typ.)
- Matched propagation delay for all channels
- Shoot-through (cross-conduction) protection
- Under-voltage lockout protection (UVLO)
- Over-current protection (OCP)
- Fault output corresponding to UV (Vcc supply) and OCP
- Shut-down of all channels during fault conditions
- Adjustable fault output duration time
- 3.3V / 5V CMOS and TTL inputs logic compatible
- Input logic: Schmitt trigger receiver circuit (Active high)

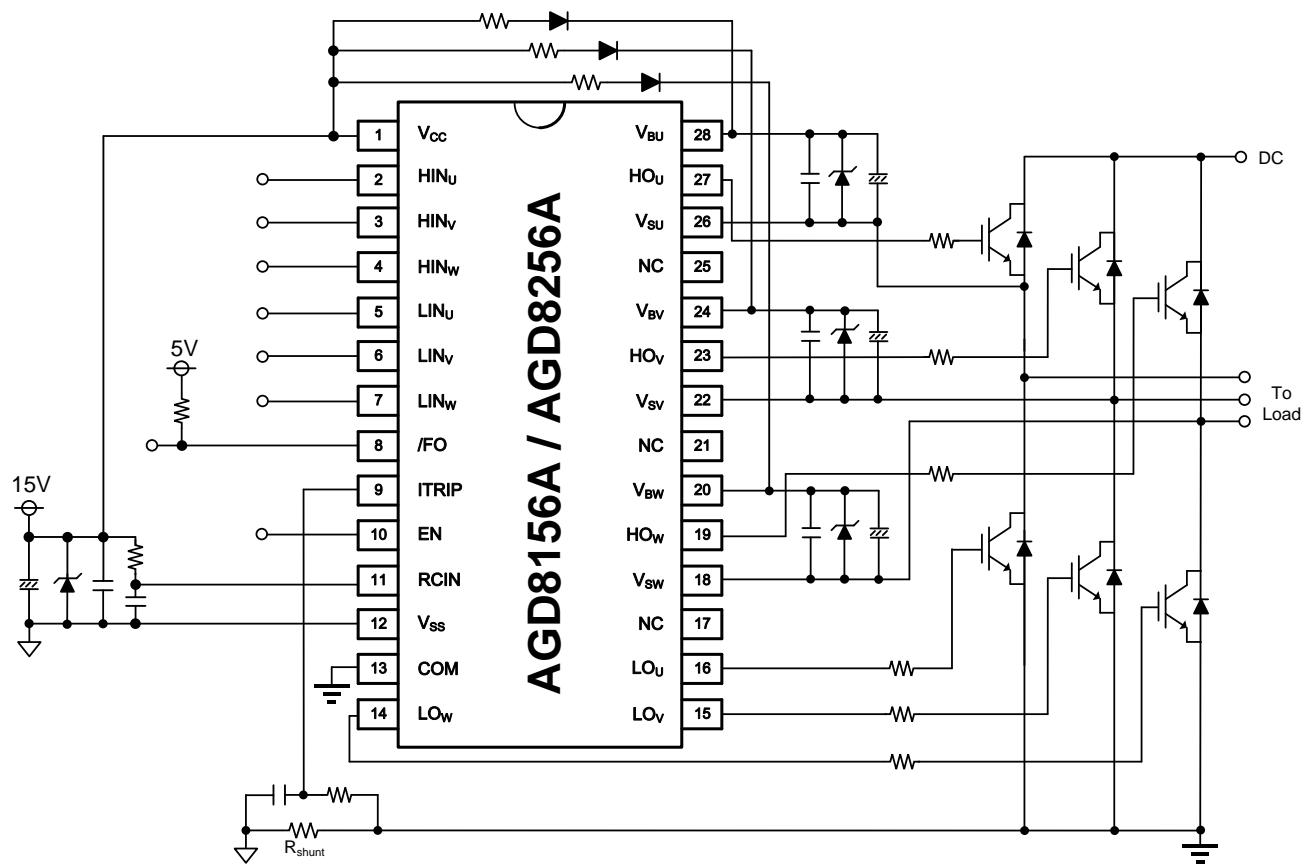
Applications

- 3-phase motor drives
- Home appliances
- IGBT and power MOS gate driver for general purpose

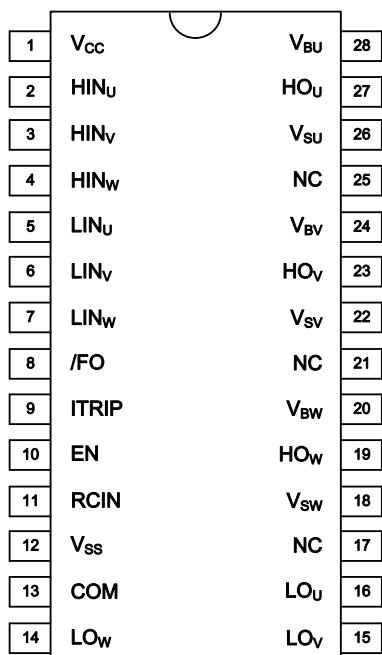
Ordering Information

Part Number	Temperature Range	Package
AGD8156A	-40°C to 125°C	SOP-28L
AGD8256A	-40°C to 125°C	SOP-28L

Typical Application Circuit



Pin Configuration



SOP-28L
(Top View)

Pin Description

Pin Number	Pin Name	Pin Function
1	V _{CC}	Low-Side Supply Voltage
2	HIN _U	High-Side Logic Input (U-Phase)
3	HIN _V	High-Side Logic Input (V-Phase)
4	HIN _W	High-Side Logic Input (W-Phase)
5	LIN _U	Low-Side Logic Input (U-Phase)
6	LIN _V	Low-Side Logic Input (V-Phase)
7	LIN _W	Low-Side Logic Input (W-Phase)
8	/FO	Fault Output with Open Drain (Indicates Over-Current and V _{CC} UVLO)
9	ITRIP	Analog Input for Over-Current Shutdown
10	EN	Enable I/O Functionality (Positive Logic)
11	RCIN	External RC-Network Input used to define Fault Output Duration Time
12	V _{SS}	Logic Ground
13	COM	Power Ground
14	LO _W	Low-Side Driver Output (W-Phase)
15	LO _V	Low-Side Driver Output (V-Phase)
16	LO _U	Low-Side Driver Output (U-Phase)
17	NC	No Connection
18	V _{SW}	High-Side Floating Supply Offset Voltage (W-Phase)
19	HO _W	High-Side Driver Output (W-Phase)

Pin Description (*continued*)

Pin Number	Pin Name	Pin Function
20	V_{BW}	High-Side Floating Supply Voltage (W-Phase)
21	NC	No Connection
22	V_{SV}	High-Side Floating Supply Offset Voltage (V-Phase)
23	HO_V	High-Side Driver Output (V-Phase)
24	V_{BV}	High-Side Floating Supply Voltage (V-Phase)
25	NC	No Connection
26	V_{SU}	High-Side Floating Supply Offset Voltage (U-Phase)
27	HO_U	High-Side Driver Output (U-Phase)
28	V_{BU}	High-Side Floating Supply Voltage (U-Phase)

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute values referenced to V_{SS}, unless otherwise stated in the table.

Symbol	Parameter	Min.	Max.	Units
V _{CC}	Low-Side Supply Voltage	-0.3	20 ⁽¹⁾	V
V _{IN}	Logic Input Voltage (LIN, HIN)	V _{SS} -0.3	V _{CC} +0.3	
V _{ITRIP}	ITRIP Input Voltage	V _{SS} -0.3	V _{SS} +5.2	
V _{EN}	Enable Input Voltage	V _{SS} -0.3	V _{SS} +5.2	
V _{RCIN}	RCIN Input Voltage	V _{SS} -0.3	V _{CC} +0.3	
V _B	High-Side Floating Supply Voltage	-0.3	620	
V _S	High-Side Floating Supply Offset Voltage	V _B -20 ⁽¹⁾	V _B +0.3	
V _{HO}	High-Side Driver Output Voltage	V _S -0.3	V _B +0.3	
V _{LO}	Low-Side Driver Output Voltage	COM-0.3	V _{CC} +0.3	
V _{FO}	Fault Output Voltage	V _{SS} -0.3	V _{CC} +0.3	
COM	Power Ground	V _{CC} -25	V _{CC} +0.3	
dV _S /dt	V _S Offset Voltage Slew Rate ⁽²⁾	-	50	V/ns
PW _{HIN}	High-Side Input Pulse Width	500	-	ns
P _D	Package Power Dissipation @ T _A ≤ 25°C	-	1.6	W
R _{th(j-a)}	Thermal Resistance, Junction to Ambient	-	78	°C/W
T _J	Junction Temperature	-	150	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	-	300	
ESD	Human Body Model	2		kV

Notes:

1. An internal 20 V zener diode is integrated to clamp each supply voltage.
2. Not subject of production test, verified by characterization.

Recommended Operating Ratings

The device is not guaranteed to operate beyond the Recommended Operating Conditions. All voltage parameters are absolute voltages referenced to V_{SS} , unless otherwise specified. The offset rating is tested with supplies of $(V_{CC} - COM) = (V_B - V_S) = 15V$.

Symbol	Parameter		Min.	Max.	Units
V_{CC}	Low-Side Supply Voltage	AGD8156A	10	20	V
		AGD8256A	13.2	20	
V_{IN}	Logic Input Voltage (LIN, HIN)		V_{SS}	$V_{SS}+5$	
V_{EN}	Enable Input Voltage		V_{SS}	$V_{SS}+5$	
V_B	High-Side Floating Supply Voltage	AGD8156A	V_S+10	V_S+20	
		AGD8256A	$V_S+13.2$	V_S+20	
V_S	High-Side Floating Supply Offset Voltage ⁽³⁾		COM-6	600	
$V_{S(t)}$	Transient High-Side Floating Supply Voltage ⁽⁴⁾		-50	600	
V_{HO}	High-Side Driver Output Voltage		V_S	V_B	
V_{LO}	Low-Side Driver Output Voltage		COM	V_{CC}	
COM	Power Ground		-5	5	
V_{FO}	Fault Output Voltage		V_{SS}	V_{CC}	
V_{RCIN}	RCIN Input Voltage		V_{SS}	V_{CC}	
V_{ITRIP}	ITRIP Input Voltage		V_{SS}	$V_{SS}+5$	
T_A	Ambient Temperature		-40	125	°C

Notes:

3. Logic operation for V_S of -6V to 600V. Logic state held for V_S of -6V to $-V_{BS}$.
4. Operational for transient negative V_S of $V_{SS}-50V$ with a 50ns pulse width, which is guaranteed by design.

Static Electrical Characteristics

$V_{CC} = V_{BS} = 15V$. $T_A = 25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
UV _{CC+}	V_{CC} Under-Voltage Positive Going Threshold	AGD8156A	8.0	8.9	9.8	V
		AGD8256A	10.8	11.9	13.0	
UV _{CC-}	V_{CC} Under-Voltage Negative Going Threshold	AGD8156A	7.4	8.2	9.0	
		AGD8256A	10.3	11.4	12.5	
UV _{CChys}	V_{CC} Under-Voltage Hysteresis	AGD8156A	-	0.7	-	
		AGD8256A	-	0.5	-	
UV _{BS+}	V_{BS} Under-Voltage Positive Going Threshold	AGD8156A	8.0	8.9	9.8	
		AGD8256A	10.0	11.0	12.0	
UV _{BS-}	V_{BS} Under-Voltage Negative Going Threshold	AGD8156A	7.4	8.2	9.0	
		AGD8256A	9.0	10.0	11.0	
UV _{BShys}	V_{BS} Under-Voltage Hysteresis	AGD8156A	-	0.7	-	
		AGD8256A	-	1.0	-	
I _{LK}	High Side Floating Supply Leakage Current (per 1-Phase)	$V_B=V_S=600V$	-	-	50	µA

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I _{QBS}	Quiescent V _{BS} Supply Current (per 1-Phase)	V _{IN} =0V (all inputs are in the off state)	-	70	120	mA
I _{QCC}	Quiescent V _{CC} Supply Current (per 1phase)		-	0.3	1	
V _{OH}	High Level Output Voltage Drop, V _{BIAS} - V _O	I _O =20mA, V _{IN} =5V	-	0.9	1.4	V
V _{OL}	Low Level Output Voltage Drop, V _O	I _O =20mA, V _{IN} =0V	-	0.4	0.6	
I _{O+}	Output High Current with Capacitive Load	C _L =10nF	120	200	-	mA
I _{Opk+}	Peak Output High Short Circuit Pulsed Current	V _O =0V, PW≤10μs (Single Pulse)	-	220	-	
I _{O-}	Output Low Current with Capacitive Load	C _L =10nF	220	350	-	
I _{Opk-}	Peak Output Low Short Circuit Pulsed Current	V _O =15V, PW≤10μs (Single Pulse)	-	375	-	
V _{IH}	High Level Input Voltage		2.5	-	-	V
V _{IL}	Low Level Input Voltage		-	-	0.8	
V _{CLAMP}	Input Clamp Voltage (LIN, HIN, ITRIP, EN)	I _{IN} =100μA	5.2	5.6	5.9	
I _{HIN+}	Input Bias Current	V _{HIN} =5V	-	650	850	μA
I _{HIN-}	Input Bias Current	V _{HIN} =0V	-	-	1	
I _{LIN+}	Input Bias Current	V _{LIN} =5V	-	650	850	
I _{LIN-}	Input Bias Current	V _{LIN} =0V	-	-	1	
V _{RCIN,TH}	RCIN Positive Going Threshold		-	8	-	V
I _{RCIN}	RCIN Input Bias Current	V _{RCIN} =0V or 15V	-	-	1	μA
R _{RCIN,ON}	RCIN Low On-Resistance	I=1.5mA	-	50	100	Ω
V _{IT,TH+}	ITRIP Positive Going Threshold		0.42	0.46	0.5	V
V _{IT,TH-}	ITRIP Negative Going Threshold		-	0.4	-	
V _{IT,Hys}	ITRIP Hysteresis		-	0.06	-	
I _{ITRIP+}	High ITRIP Input Bias Current	V _{ITRIP} =4V	-	5	40	μA
I _{ITRIP-}	Low ITRIP Input Bias Current	V _{ITRIP} =0V	-	-	1	
V _{EN,TH+}	EN Positive Going Threshold		-	-	2.5	V
V _{EN,TH-}	EN Negative Going Threshold		0.8	-	-	
I _{EN+}	High EN Input Bias Current	V _{EN} =5V	-	5	40	μA
I _{EN-}	Low EN Input Bias Current	V _{EN} =0V	-	-	1	
R _{F0,ON}	Fault Low On-Resistance	I=1.5mA	-	50	100	Ω

Dynamic Electrical Characteristics

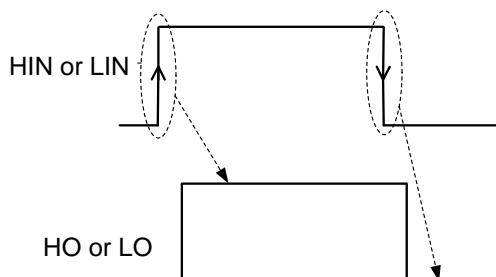
V_{BIAS} (V_{CC} or V_{BS}) = 15V, $C_L = 1000pF$ and $T_A = 25^\circ C$ unless otherwise specified.

Symbol	Definition		Conditions	Min.	Typ.	Max.	Units	
t_{ON}	Turn-On Propagation Delay		$V_{IN}=0V$ or $5V$	400	530	750	ns	
t_{OFF}	Turn-Off Propagation Delay			400	530	750		
t_R	Turn-On Rise Time			-	125	190		
t_F	Turn-Off Fall Time			-	50	75		
$t_{IN,FLT}$	Input Filter Time (LIN, HIN) ⁽⁵⁾			200	350	510		
t_{EN}	EN Low to Output Shutdown Propagation Delay			250	460	650		
$t_{EN,FLT}$	EN Input Filter Time		$V_{IN}=5V$ $V_{EN}=5V \rightarrow 0V$	100	200	-	ms	
t_{FOd}	Fault Output Duration Time (RCIN: $C = 1nF$, $R = 2M\Omega$)			1.3	1.65	-		
t_{ITRIP}	ITRIP to Output Shutdown Propagation Delay	Low Side		420	620	970	ns	
		High Side		600	800	1150	ns	
$t_{IT,FLT}$	ITRIP Filter Time		$V_{ITRIP}=1V$ $V_{IN}=5V$, $V_{FO}=5V$ (10k Ω pull-up)	-	400	-	ns	
t_{FO}	ITRIP to FO Propagation Delay			400	600	950	ns	
DT	Dead Time ⁽⁶⁾			100	275	420	ns	
MT	Matching Delay Time (t_{ON} , t_{OFF}) ⁽⁷⁾		$ t_{ON(HO)} - t_{ON(LO)} $ or $ t_{OFF(HO)} - t_{OFF(LO)} $	-	-	100		
PM	Output Pulse Width Matching ⁽⁸⁾		Input pulse width=10 μs	-	-	150		

Notes:

5. The minimum width of the input pulse is recommended to exceed 500ns to ensure the filtering time of the input filter.
6. Please refer to 'Dead Time' definition of 'Function Diagram'.
7. This parameter, MT and MDT applies to all of the channels.
8. PM is defined as $|(input\ pulse\ width) - (output\ pulse\ width)|$.

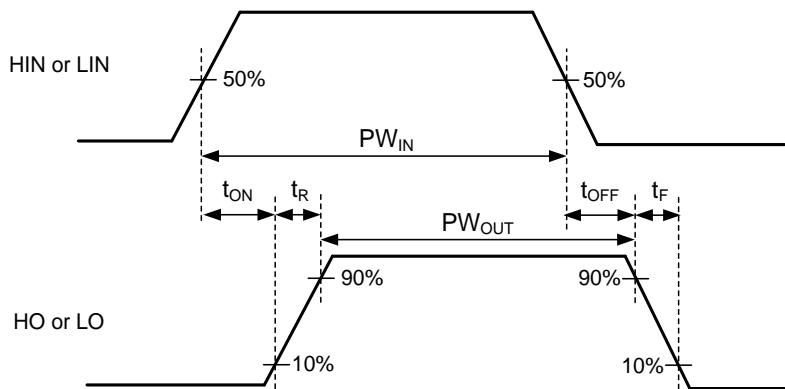
Output Activation



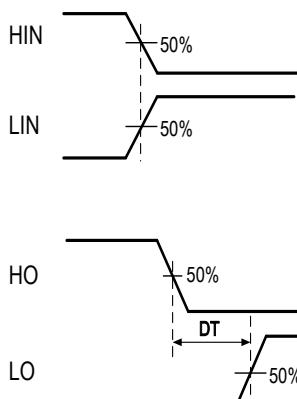
EN	HIN	LIN	HO	LO
L	L or H	L or H	L	L
H	H	L	H	L
	L	H	L	H

Note: Output signal (HO or LO) is triggered by the edge of input signal.

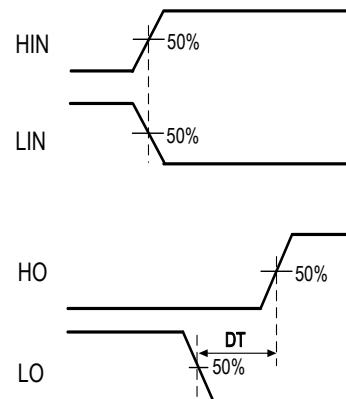
Input / Output Timing Diagram



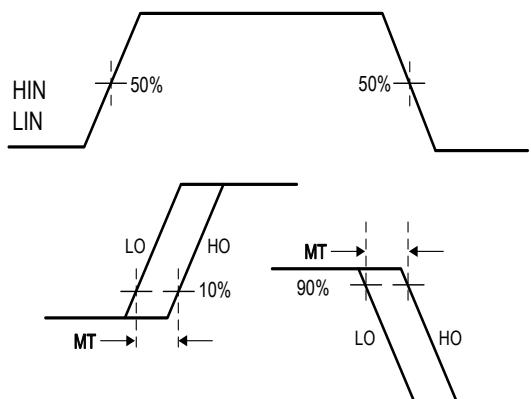
Dead Time Activation



<HIN off and LIN on>



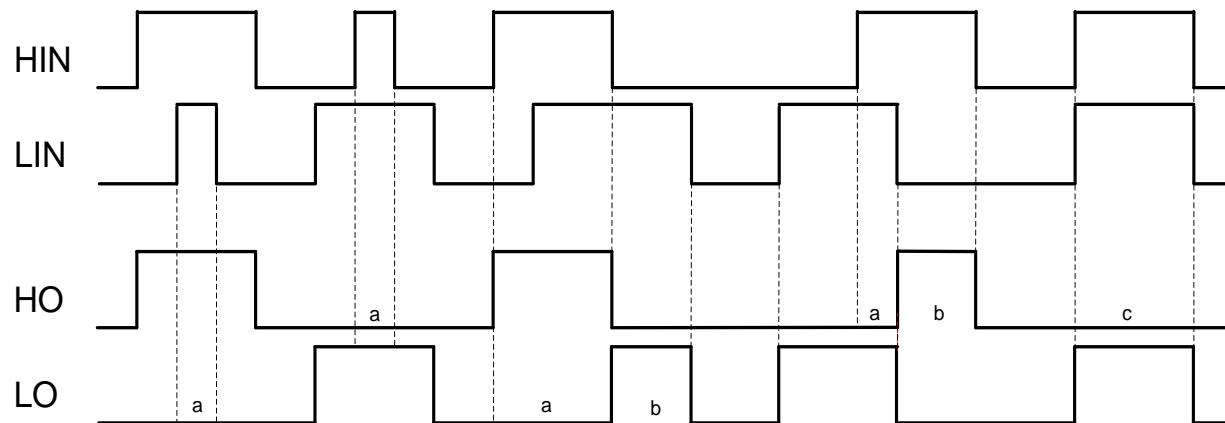
<HIN on and LIN off>



<Delay Matching Waveform Definition>

Function Timing Diagram

A. Illustration of Shoot-Through (Cross-Conduction) Protection Logic

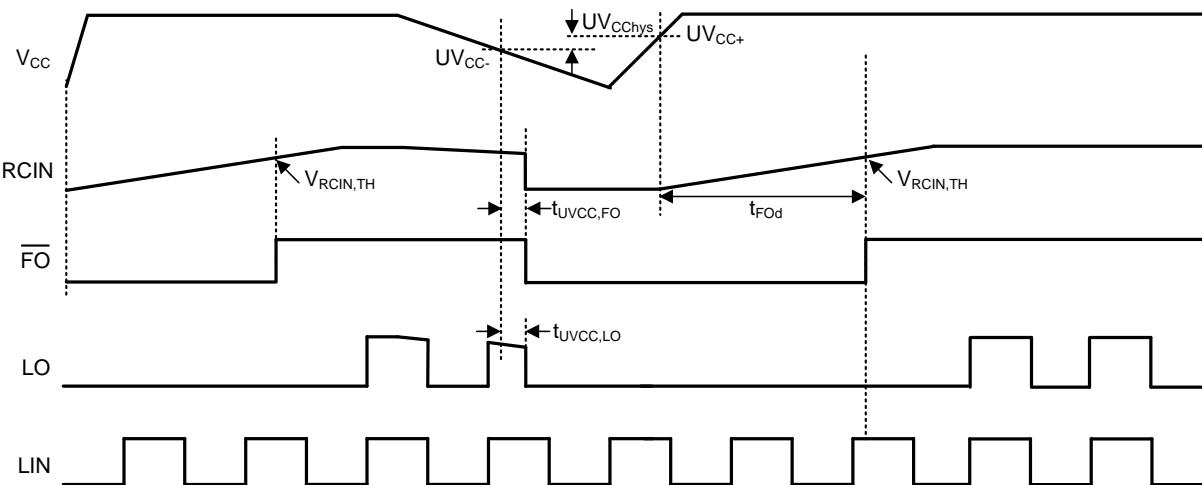


Note:

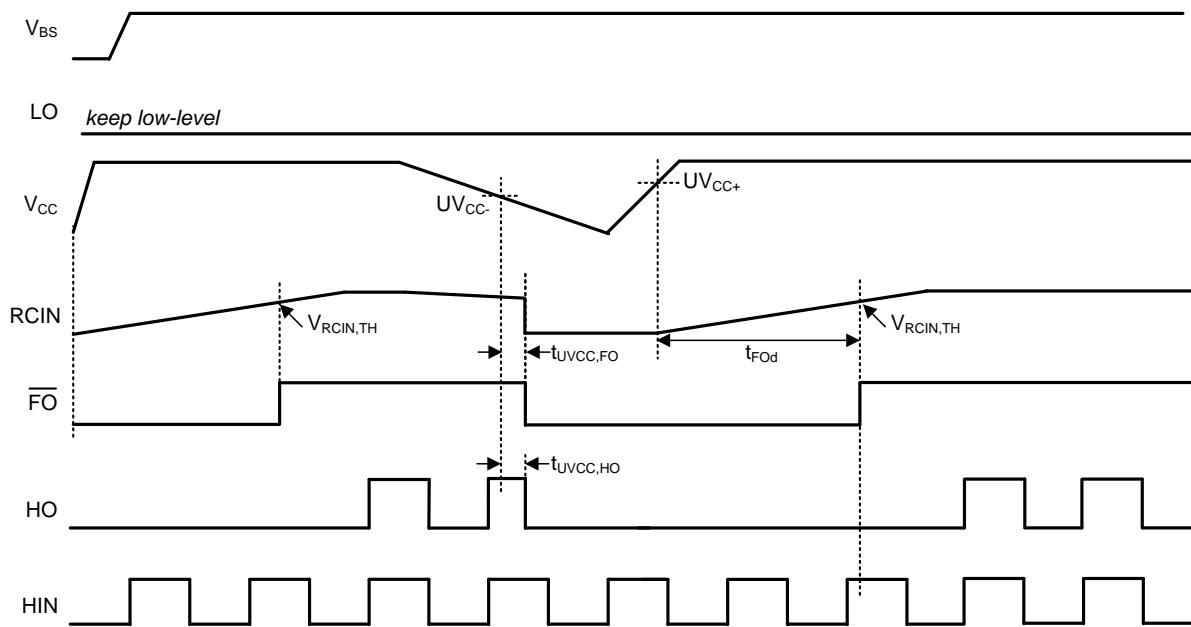
- When one output (high or low side) is turned on, the other side turn-on input is ignored.
- If both outputs are changed simultaneously, the turn-on activation is done by the internal dead time of 275ns typ.
(For more information, please refer to below 'Dead Time' section.)
- When high-side (HIN) and low-side (LIN) have turn-on inputs at the same time, low-side (LIN) has the priority.

B. V_{CC} (V_{BS}) Supply Under-Voltage (UV) Lockout Timing Diagram

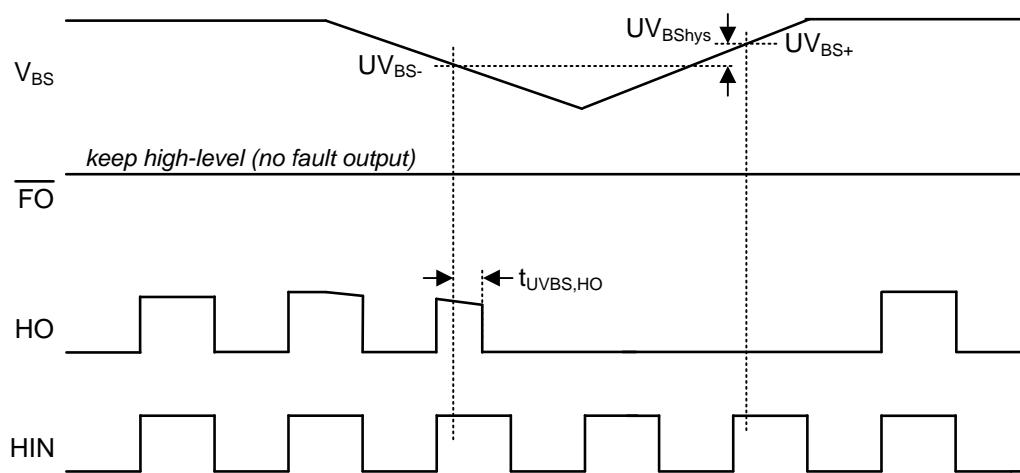
a. LO operation by V_{CC} under-voltage protection



b. HO operation by V_{CC} under-voltage protection

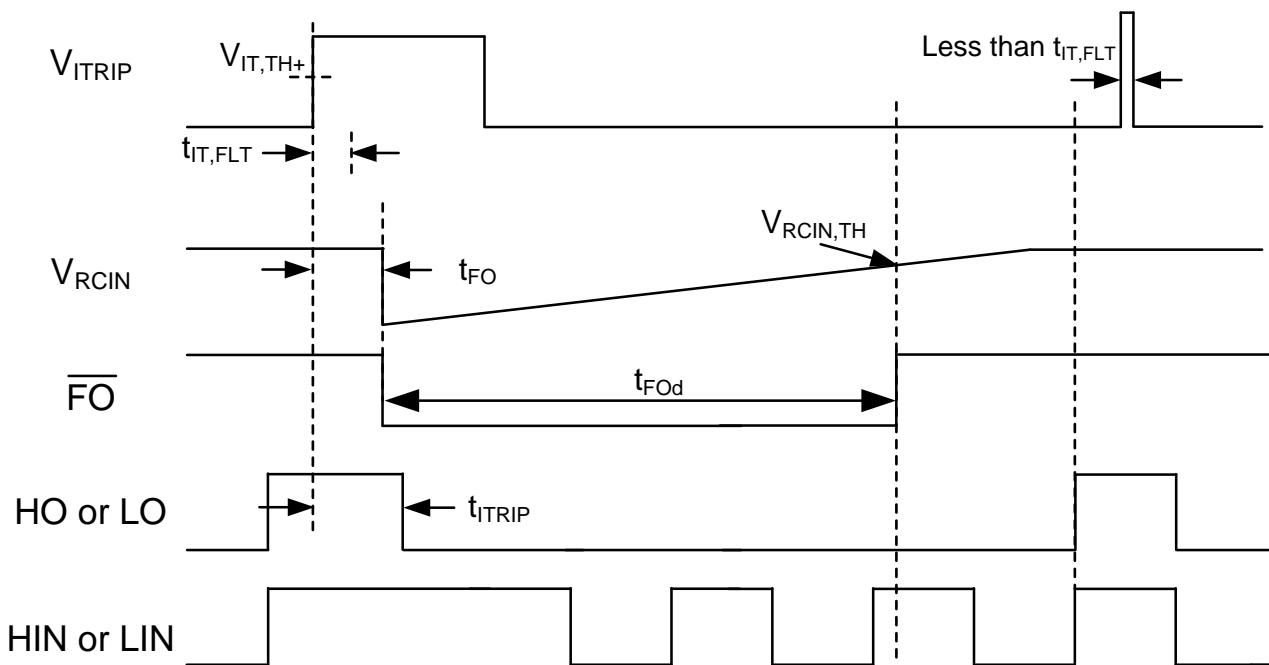


c. V_{BS} supply under-voltage (UV) lockout timing diagram

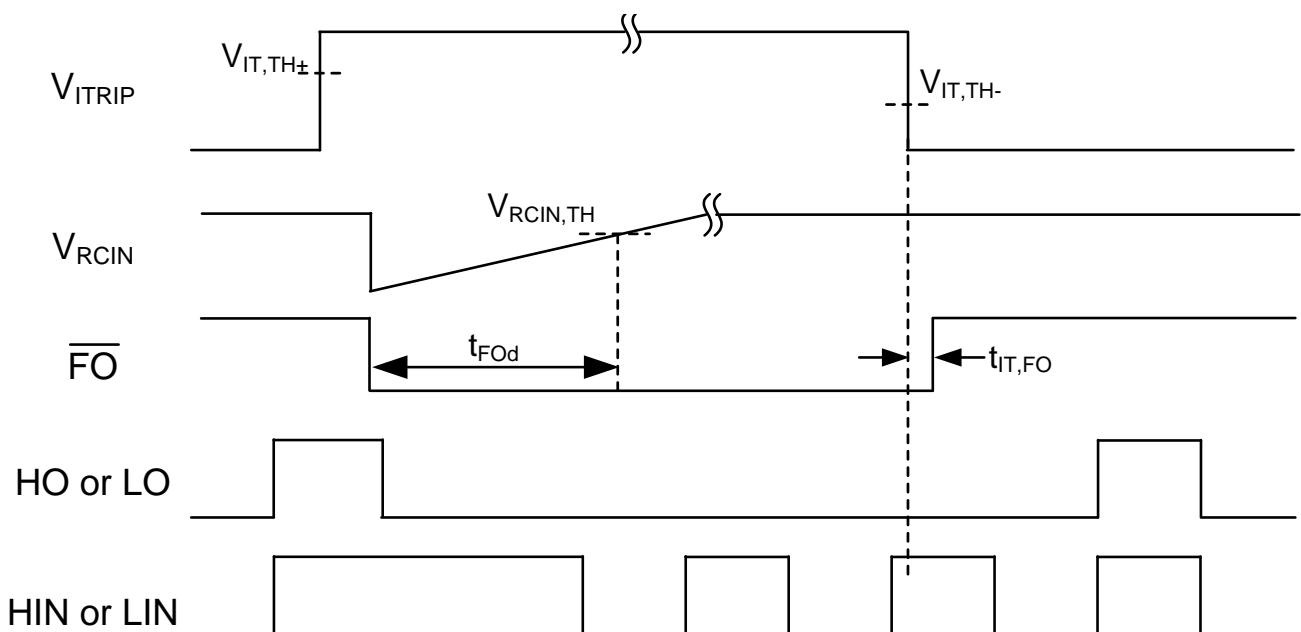


C. Over-Current Protection

- a. When ITRIP voltage rises higher than positive going threshold for $t < t_{FOd}$

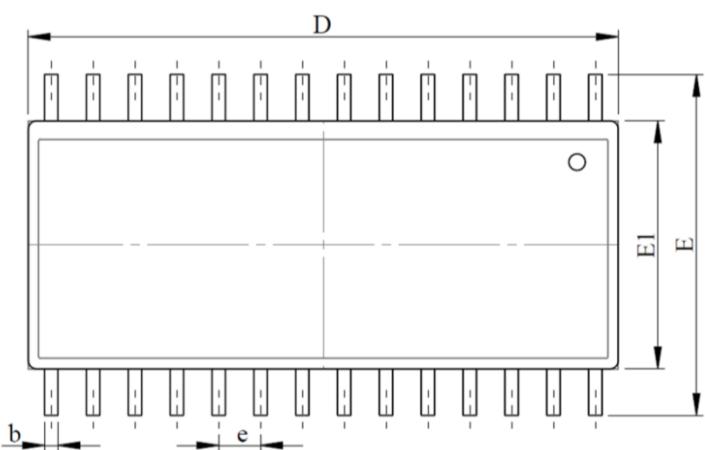


- b. When ITRIP voltage keeps longer than t_{FOd}

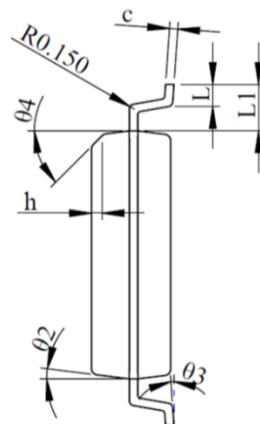


Package Dimensions, SOP-28L

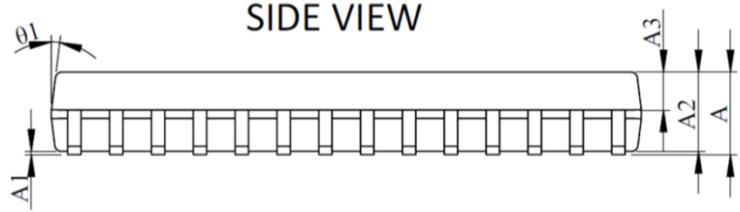
TOP VIEW



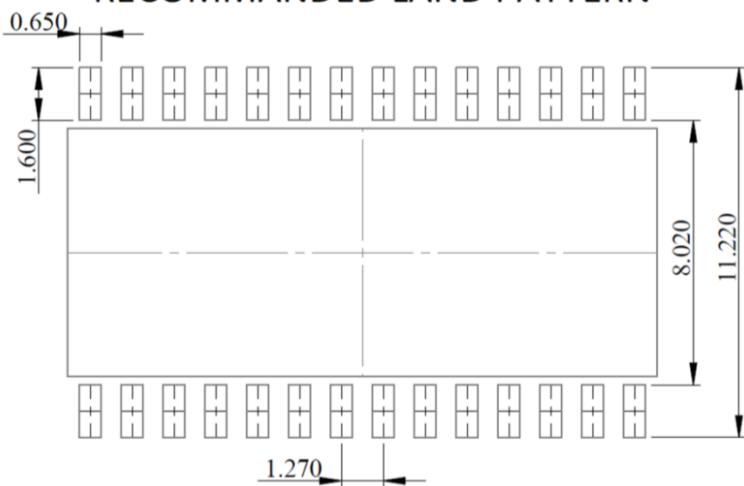
SIDE VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN



SYMBOL	DIMENSION IN MM		
	MIN.	NOM.	MAX.
A	2.354	---	2.654
A1	0.1	---	0.3
A2	2.254	---	2.554
A3	1	---	1.3
D	17.8	17.9	18
E	10.1	10.34	10.58
E1	7.42	7.52	7.57
L	0.405	0.705	0.905
L1	1.21	1.41	1.61
e	1.27TYP.		
b	0.41TYP.		
c	0.254TYP.		
theta1	7°TYP.		
theta2	7°TYP.		
theta3	0°	---	8°
theta4	45°TYP.		
h	0.381TYP.		

NOTES

1. CONTROLLING DIMENSION : MM.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.

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